

**GBJ35005-GBJ3510**

**Single-Phase 35.0A Glass Passivated Bridge Rectifier**

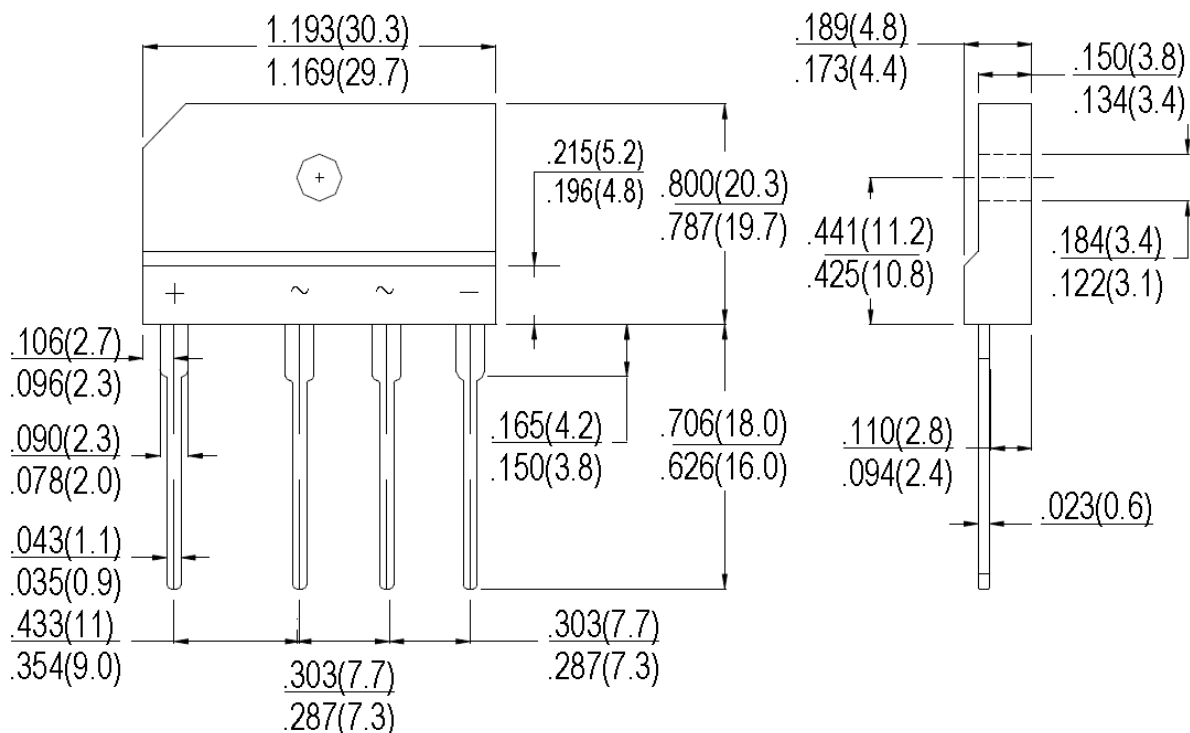
**Features:**

- Glass passivated die construction
- Low forward voltage drop
- High current capability
- High surge current capability
- Plastic material-UL flammability 94V-0

**Mechanical Data:**

- Case: GBJ, Molded plastic
- Terminals: Plated leads solderable per MIL-STD-202, Method 208
- Polarity: as marked on case
- Mounting Position: Any
- Lead Free: For RoHS / Lead Free Version

**Mechanical Dimensions: In Inches/mm**



**GBJ**

**MARKING, MOLDING RESIN**

Marking for Type Number, 1<sup>st</sup> row SSG YYWWL, 2<sup>nd</sup> row Type Number

Where YY is the manufacture year

WW is the manufacture week code

L is the wafer's Lot Number

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## GBJ35005 THRU GBJ3510

Technical Data  
Data Sheet N1805, Rev. -

Green Products

**Maximum Ratings and Electrical Characteristics** Rating at 25°C ambient temperature unless otherwise specified. Single Phase, half wave, 60Hz, resistive or inductive load.  
For capacitive load, derate current by 20%

### Maximum Ratings:

Type Number	Symbol	GBJ 35005	GBJ 3501	GBJ 3502	GBJ 3504	GBJ 3506	GBJ 3508	GBJ 3510	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_{DC}$	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{RMS}$	35	70	140	280	420	560	700	V
Average forward rectified output current (Note 1) @ $T_A = 90^\circ\text{C}$	$I_O$	35.0							A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	$I_{FSM}$	320							A

### Electrical Characteristics:

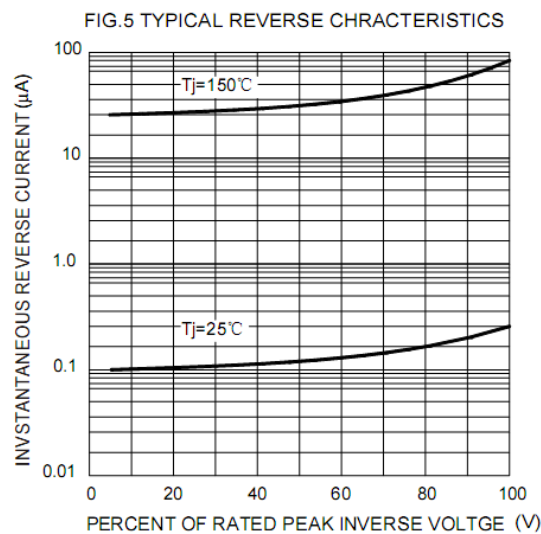
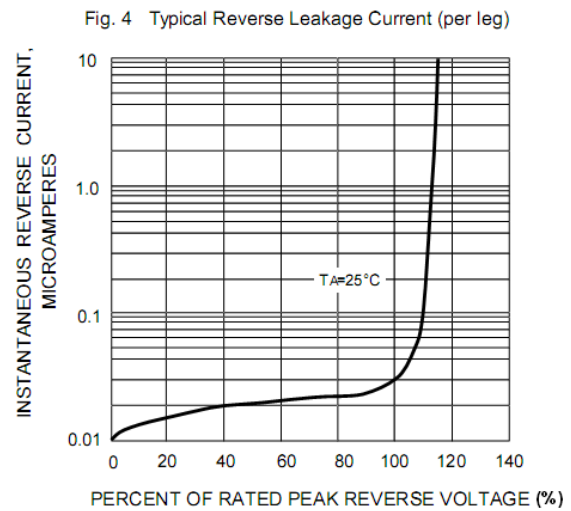
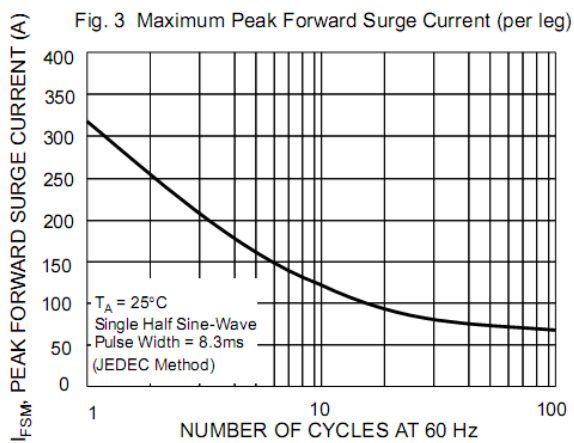
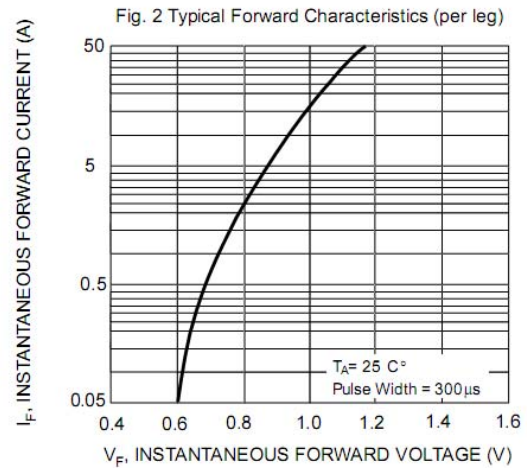
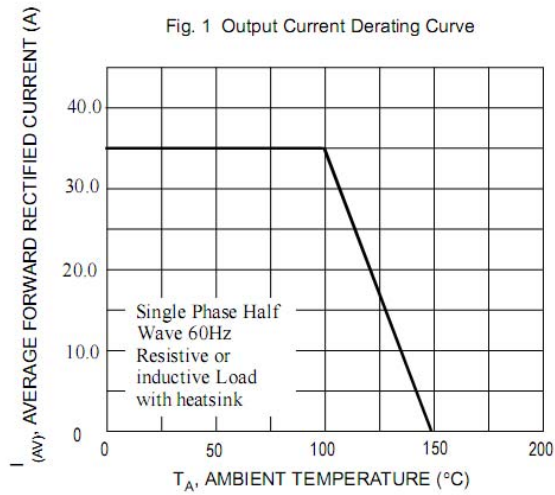
Type Number	Symbol	GBJ 35005	GBJ 3501	GBJ 3502	GBJ 3504	GBJ 3506	GBJ 3508	GBJ 3510	Unit	
Forward Voltage (per element) @ $I_F = 17.5\text{A}$ @ $I_F = 35\text{A}$	$V_{FM}$	1.0 1.1								V
Peak Reverse Current @ $T_A = 25^\circ\text{C}$ At Rated DC Blocking Voltage @ $T_A = 125^\circ\text{C}$	$I_R$	5.0 500								$\mu\text{A}$
Typical Junction Capacitance(per leg) (Note 2)	$C_J$	75								pF

### Thermal-Mechanical Specifications:

Type Number	Symbol	GBJ 35005	GBJ 3501	GBJ 3502	GBJ 3504	GBJ 3506	GBJ 3508	GBJ 3510	Unit
Between Junction and Ambient, Without heatsink	$R_{\theta JA}$	22							$^\circ\text{C}/\text{W}$
Between Junction and Case, Without heatsink	$R_{\theta JC}$	0.8							
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150							$^\circ\text{C}$
Case Style		GBJ							

Note: 1. Mounted on glass epoxy PC board with 1.3mm<sup>2</sup> solder pad.  
2. Measured at 1.0 MHz and applied reverse voltage of 5.0V D.C.

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